

RADIETE COLLABORATION MEETING @TRIUMF

11TH DECEMBER, 2019

**PRESENT STATUS OF DEVELOPMENT FOR
TUNGSTEN ALLOY, TFGR W-1.1% TIC,
AS ADVANCED TARGET MATERIAL**

**HIGH ENERGY ACCELERATOR RESEARCH ORGANIZATION,
INSTITUTE OF PARTICLE AND NUCLEAR STUDIES**

J-PARC CENTER, PARTICLE & NUCLEAR PHYSICS DIVISION

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 - TFGR W-TiC
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 - Present status of TFGR W-TiC
- Discussion to improve creep behavior in TFGR W-TiC
- Summary

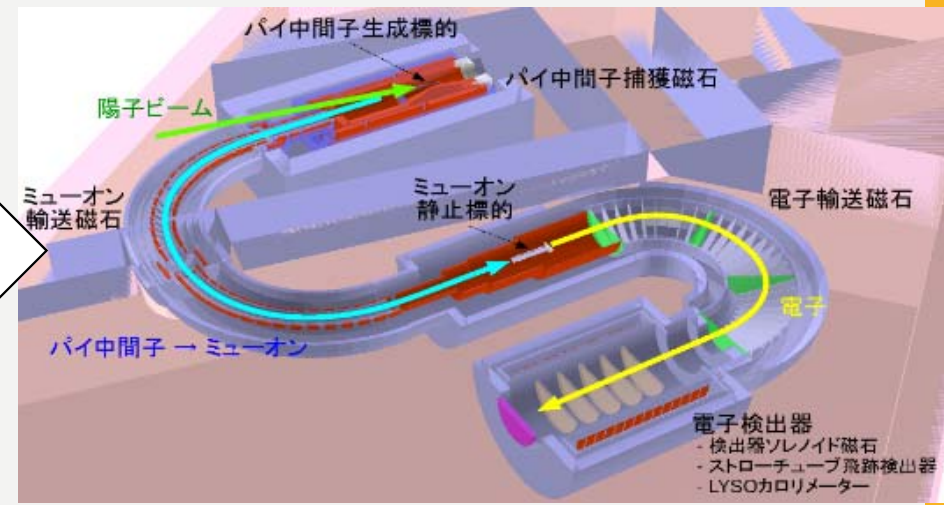
PRIVATE AFFAIR

On 1st Oct. 2019

- I moved from “KEK, IMSS, Materials and Life Science Facility, Muon Science section” to “KEK-Institute of Particle and Nuclear Studies, J-PARC-Particle and Nuclear Physics division”
- Construction of Muon Target is completed, “COMET target” next



Muon Target @MLF, J-PARC
3 GeV, 1 MW
Graphite target



COMET target @hadron facility, J-PARC
8 GeV
P1: 3.2 kW, Graphite target
P2: 56 kW, SiC or tungsten target

THIS PRESENTATION IS SUPPLIED BY

- KEK-IPNS, J-PARC-Particle and Nuclear Physics division
- COMET collaboration
- Metal Technology Co., LTD
- Sunric Co., LTD
- Ehime University, CERN, HIT- Tokyo University,,

Supported by

- MTC-KEK collaboration
- Grant-In-Aid, JSPS KAKENHI 19H01913
- Grant-In-Aid, The Small and Medium Enterprise Agency, METI
- Joint Usage/Research Center PRIUS, Ehime University, Japan

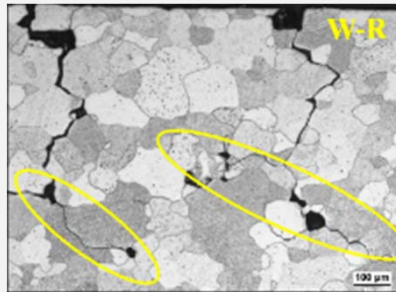


DEVELOPMENTS FOR TFGR W-TIC

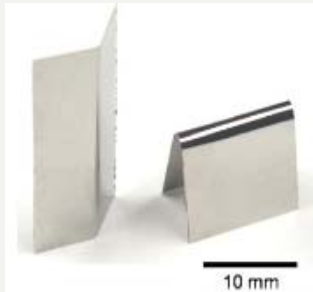
TUNGSTEN AS TARGET MATERIAL

- Expected as the target material, due to high density and high melting point
- For use of tungsten as muon production target, the boundary between cooling material and vacuum in beamline disturb transportation of muon. Thermal radiation cooling is desired. It should be used at high temperature. (COMET, mu2e, MLF TS2,,,))

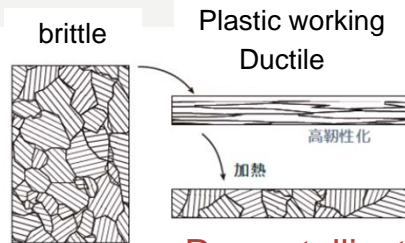
- ✓ Tungsten is brittle, because grain boundary is weak.
- ✓ Brittleness is improved by heavy plastic working.



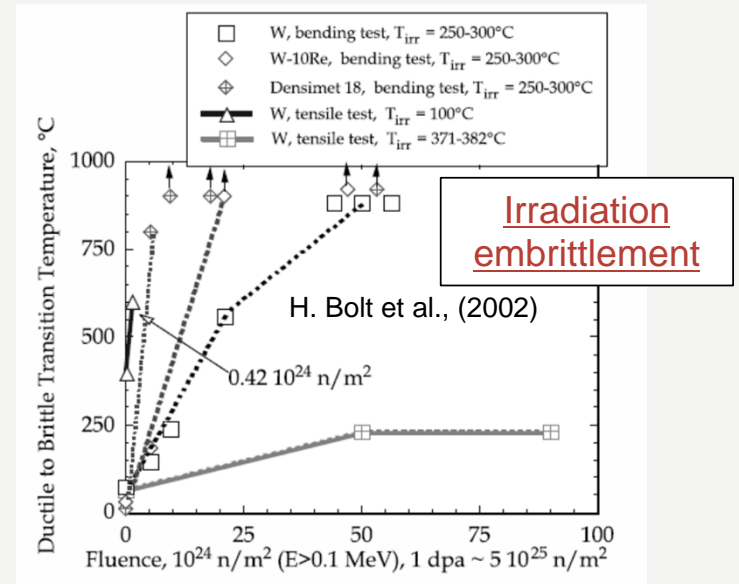
G. Pintsuk et al.



J.Reiser et al. JNM, 423 (2012) 1.



Recrystallization embrittlement



Ductile to Brittle Transition Temperature should be less than room temperature.

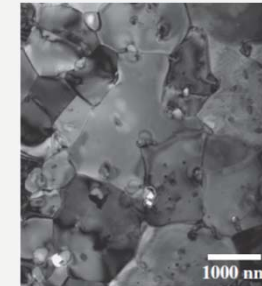
- The use of W as target material is limited by “Recrystallization embrittlement” and “Irradiation embrittlement”.

Since 2016

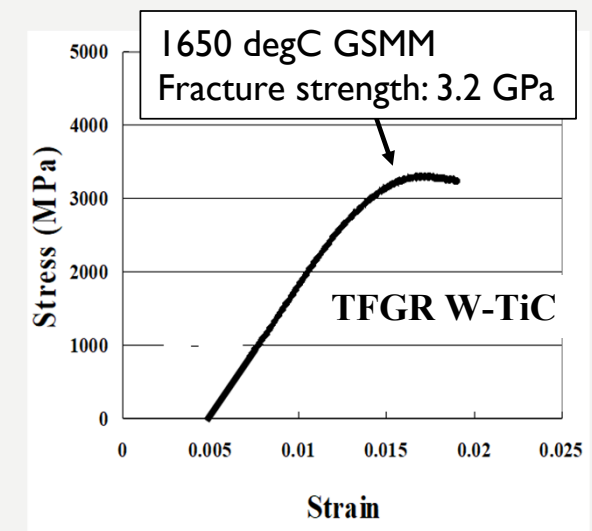
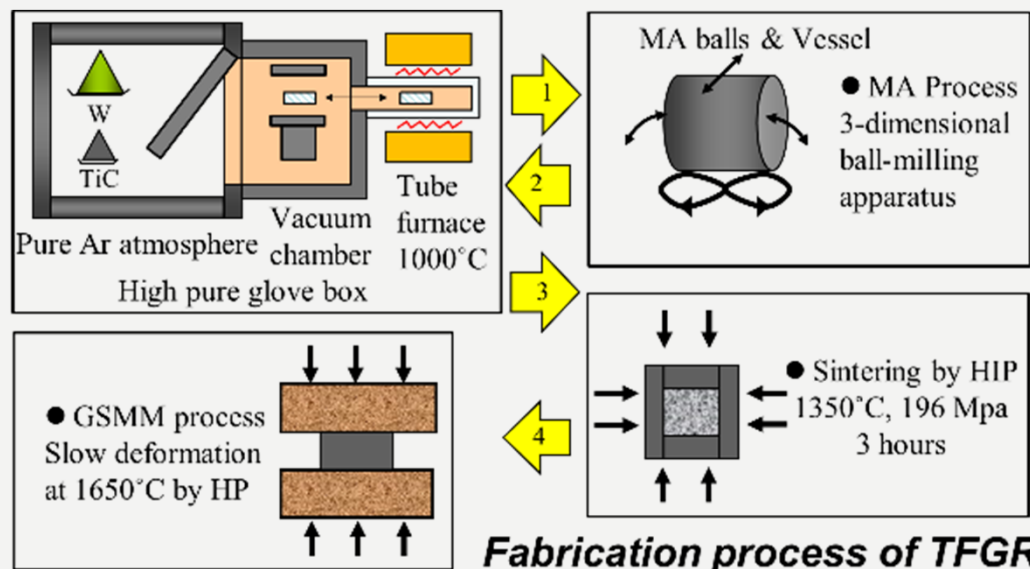
TFGR W-TiC

Toughened Fine-Gained Recrystallized W-TiC, (TFGR W-TiC) is developed by Prof. Kurishita at Tohoku University. Now the activities are transferred to KEK and Metal Technology Co. LTD collaboration.

- ❑ Equiaxed, fine grains with TiC precipitates
- ❑ GB reinforced by TiC enrichment
- ❑ No recrystallization embrittlement
- ❑ High sink density: Resistance to irradiation is anticipated.
- ❑ DBTT (nil-ductility tem.) < RT

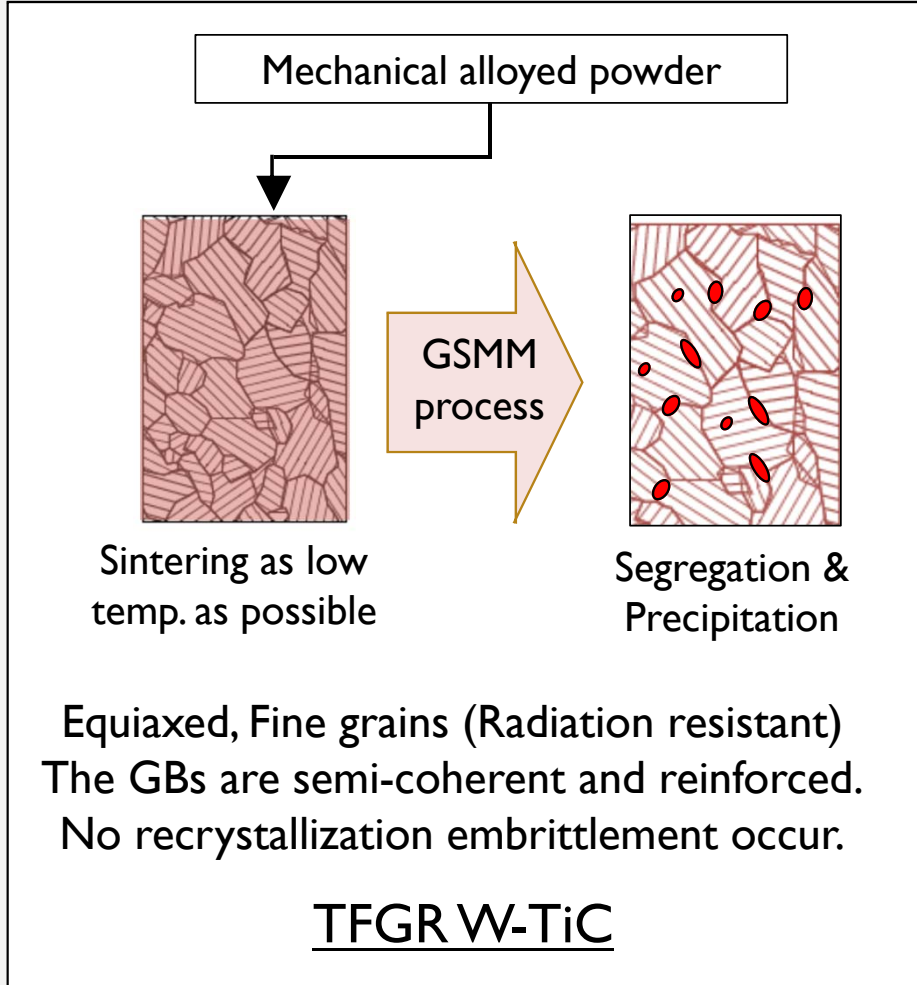
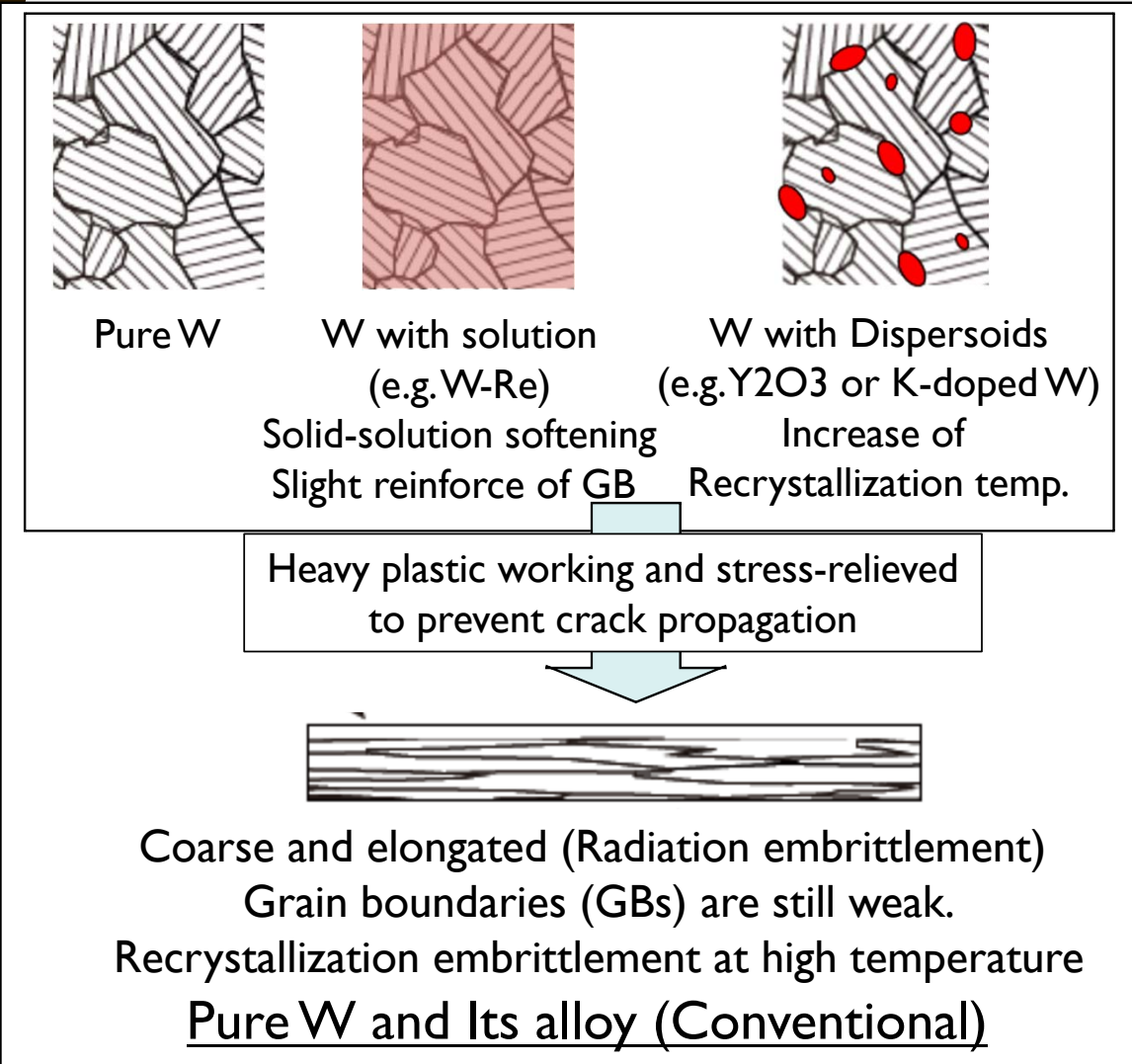


Mater. Trans. 54 (2013) 456-465.



Ductility at RT

PURE W, ITS ALLOYS, AND TFGR W-TiC



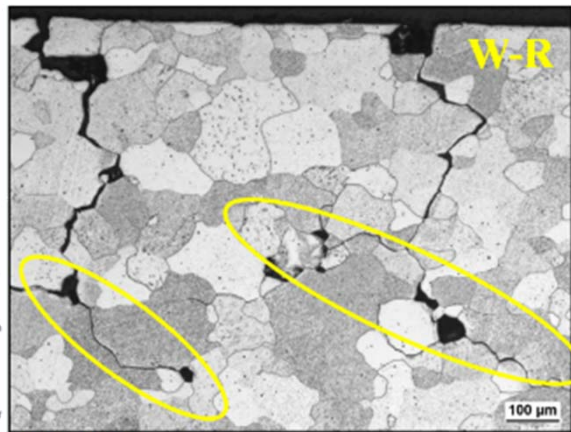
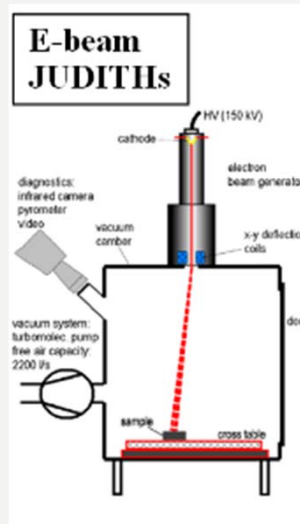
PURE W, ITS ALLOYS, AND TFGR W-TiC

Characterization item	Pure W	W-Re	W-Y ₂ O ₃ or K-doped	TFGR W-TiC
How Strengthened	Hot rolling etc. & Grain size	Hot rolling etc. & Solution	Hot rolling etc. & Dispersion	Segregation & Dispersion (Precipitation)
Recrystallization embrittlement				
Recrystallization embrittlement	Yes	Yes	Yes	No
Expected usable maximum temp.	1200-1300 °C	1500 °C	1500 °C	1800 °C (in UHV) or higher *
GB in the recrystallized state	Weak (not reinforced)	Slightly reinforced by Re	Very weak (not reinforced)	Reinforced by TiC _x (Semi coherent)
DBTT in the recrystallized state	Higher than RT	Around RT	Higher than RT	Around RT
Irradiation embrittlement				
Grain appearance	Elongated, Coarse	Elongated, Coarse	Elongated, Coarse	Equiaxed, fine grains in recrystallized state
Radiation damage	Vulnerable	Vulnerable	Vulnerable	Resistant (anticipated)

* Creep behavior must be considered, as discussed later

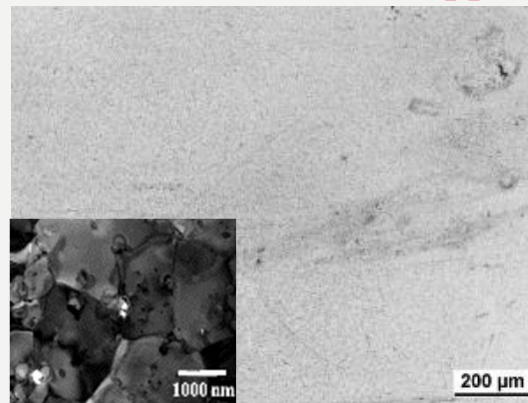
TFGR W-TiC

Electron beam heating,
 $A = 16 \text{ mm}^2$, $t = 1 \text{ ms}$,
 $P = 1.1 \text{ GW/m}^2$
 $\Delta T \approx 2000^\circ\text{C}$
 $T_{\text{base}} = 100^\circ\text{C}$, $n = 100$



PLATE

TFGR W-1.1TiC/H-160ppmO



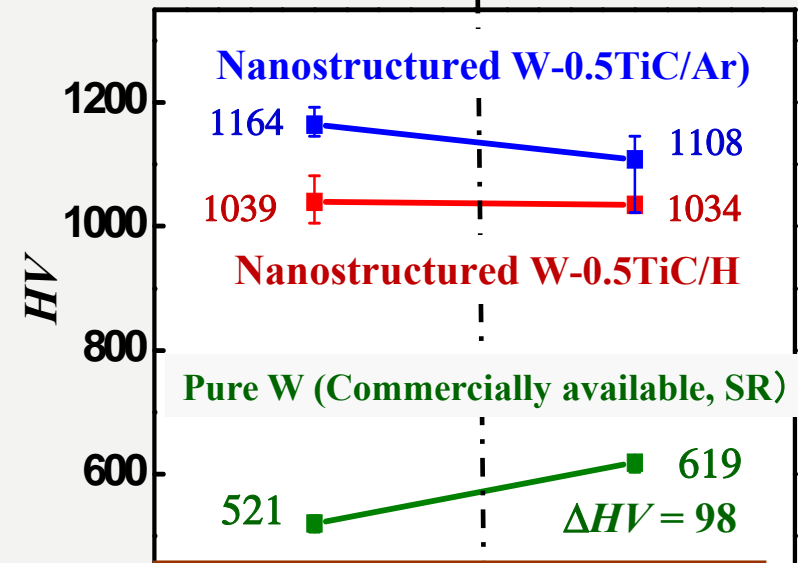
G. Pintsuk et al. Phys. Scr. T145 (2011) 014060.

Promising result of electron beam heating test.

$T_{\text{irr}} = 873\text{K}$, $2 \times 10^{24} \text{ n/m}^2$ ($E_n > 1 \text{ MeV}$),
 0.08 dpa, JMTR

Vickers microhardness

Before irr. | After irr.



▪ No radiation hardening

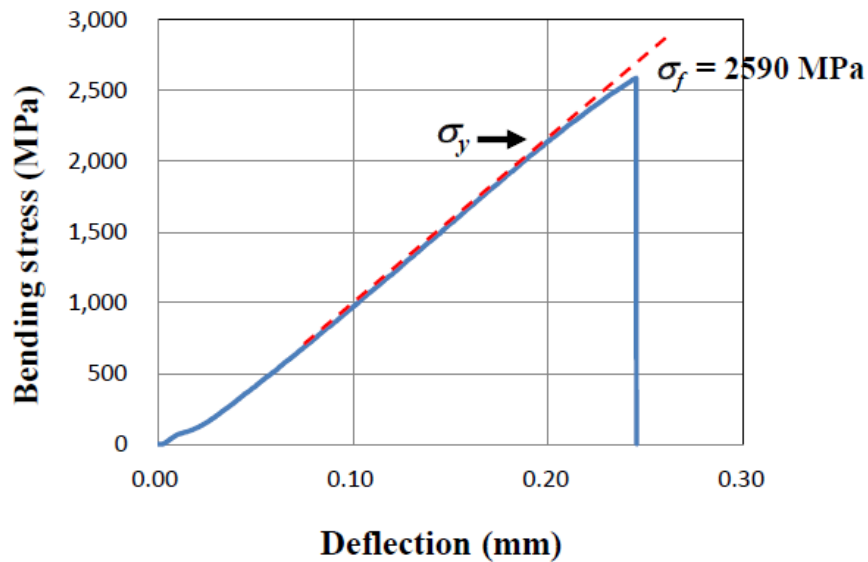
H.Kurishita et al. JNM 377 (2008) 34.

Limited, but promising result of HE-neutron irradiation.

Further studies are planned, HIT or next BLIP?

RECALL OF REPORT AT RADIATE CM, CERN, 2018

- The development of TFGR was transferred to KEK-MTC collaboration.
- Restoration of TFGR was realized.



- High fracture strength, 2.6 GPa
- Ductility at RT

- Oxygen impurity should be decreased.
- MA process for 72 hours was not sufficient.

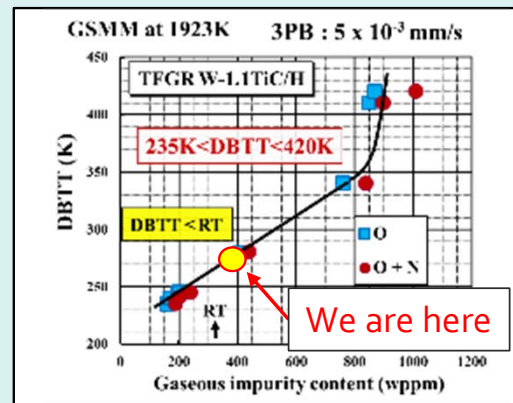
Construction of new dedicated apparatuses



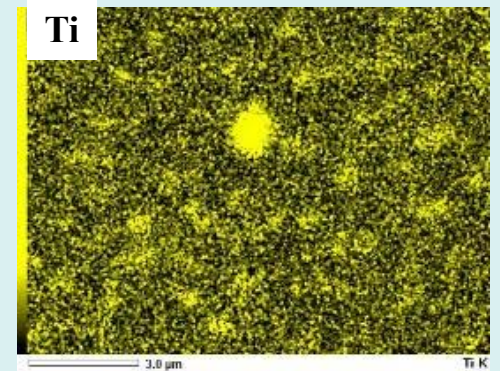
High purity glove box



Mechanical Alloying in vac.



H. Kurishita, Phys. Scr. T159 (2014) 014032.

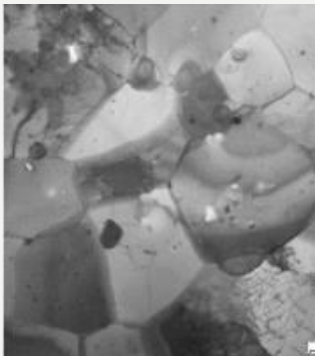


EDS~ Remaining Ti

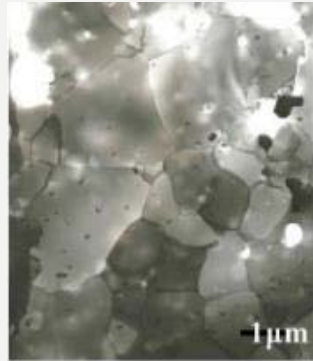
Future Prospect of TFGR W-TiC

Pursuit of higher performance

W-TiC \Rightarrow W-TaC or ??



W-2.2TaC



W-3.3TaC

Material	TaC	TaO ₂	W ₂ C	G.S.	DBTT
W-2.2TaC	130	160	560	2.2 μm	330K
W-3.3TaC	80	130	-	1.2 μm	420K

(nm)

H. Kurishita et al. Phys. Scr. T159 (2014)014032.

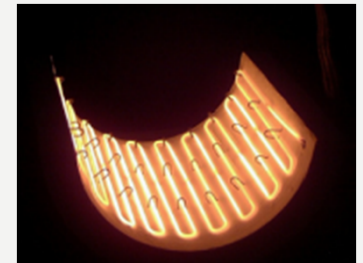
Developments for Mass production & Industrial use by Academic Industrial Collaboration

- Metal Technology Co., LTD
- Sunric Co., LTD.
- And several vendors as advisors

Objective

- Heater material in vapor deposition for manufacturing of semi-conductors
- Anode in lamp for lithography

Supported by the Small and Medium Enterprise Agency, METI



Investigation of radiation damage

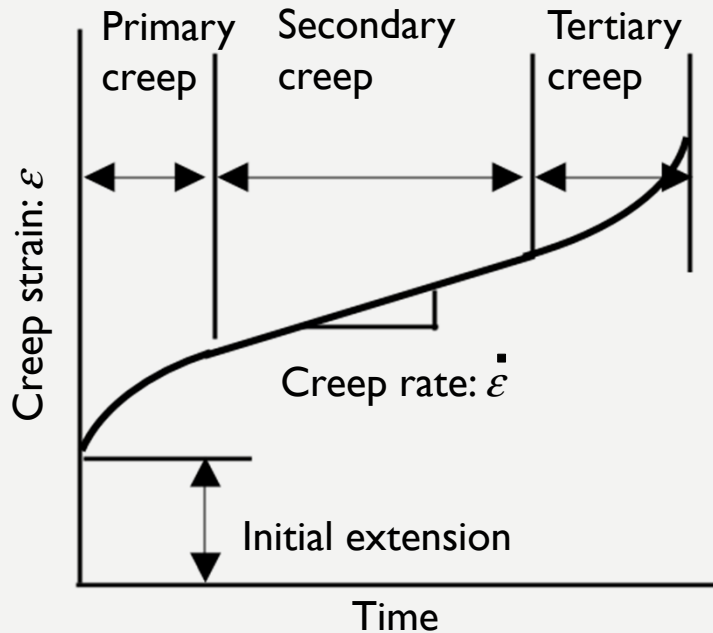
- Irradiation damage (dpa), by HIT-Tokyo-U
- Next BLIP or other neutron-irradiation?
- Investigation of He, Re, Os embrittlement by ??





DISCUSSION TO IMPROVE
CREEP BEHAVIOR IN
TFGR W-TIC

FUNDAMENTAL OF CREEP BEHAVIOR



Secondary creep

$$\dot{\epsilon}_s \propto (\sigma/E)^n \exp(-Q/kT)$$

$$\dot{\epsilon}_s = \dot{\epsilon}_0 (\mu\Omega/kT)(\sigma/\mu)^n (b/d)^p (D/b^2)$$

n , p , Q are relevant to structure, stress region, and temperature region.

p , d are considered at 2nd formula.

Creep: Permanent deformation under Constant stress and Constant temperature

Primary creep (Skip in this presentation)

■ Sliding length of Dislocation

- Pure tungsten: large
- With solution or dispersion: small

n : stress exponent

d : grain size, p : exponent of inverse grain size

Q : activation energy for creep μ : rigidity

σ : stress Ω : atomic volume

E : Young's modulus b : Burgers vector

T : Absolute temperature D : diffusion coefficient

k : Boltzmann constant

RELATIONSHIP BETWEEN STRUCTURES AND CREEP MECHANISM

Structure in W and its alloys	Steady state (Secondary) creep rate						
	Creep mechanism	Controlling mechanism	Stress exponent, n	Diffusion	Q	p	
Pure W	Dislocation slip	Recovery of internal stress (disl.)	~ 5	Lattice, D_L	Q_L	0	
			~ 7	Pipe, D_p	Q_p	0	
Solution hardened (W-Re)	Dislocation slip	Solute atmosphere dragging	$3 \sim 4$	Mutual, D_m	Q_m	0	
Dispersion hardened (W-Y ₂ O ₃)	Dislocation slip	Recovery of inter. stress (particle)	> 6	Lattice, D_L	Q_L	0	
TFGR W-1.1TiC (Toughened, fine grained, recrystallized)	Dislocation slip	Recovery of inter. stress (precipitate)	> 6	Lattice, D_L	Q_m	0	
			Lattice diffusion	2	Lattice, D_L	Q_L	2
			GB diffusion	2 (1)	GB, D_{gb}	Q_{gb}	3

Secondary creep

$$\dot{\epsilon}_s \propto (\sigma/E)^n \exp(-Q/kT)$$

$$\dot{\epsilon}_s = \dot{\epsilon}_0 (\mu\Omega/kT)(\sigma/\mu)^n (b/d)^p (D/b^2)$$

- n : stress exponent
- Q : activation energy for creep
- d : grain size
- p : exponent of inverse grain size

When the grain size is fine, the effect of grain boundary sliding must be taken into account.

AIMING AT SIGNIFICANT ENHANCEMENT OF CREEP RESISTANCE IN TFGR W-TiC

Features of current TFGR W-TiC

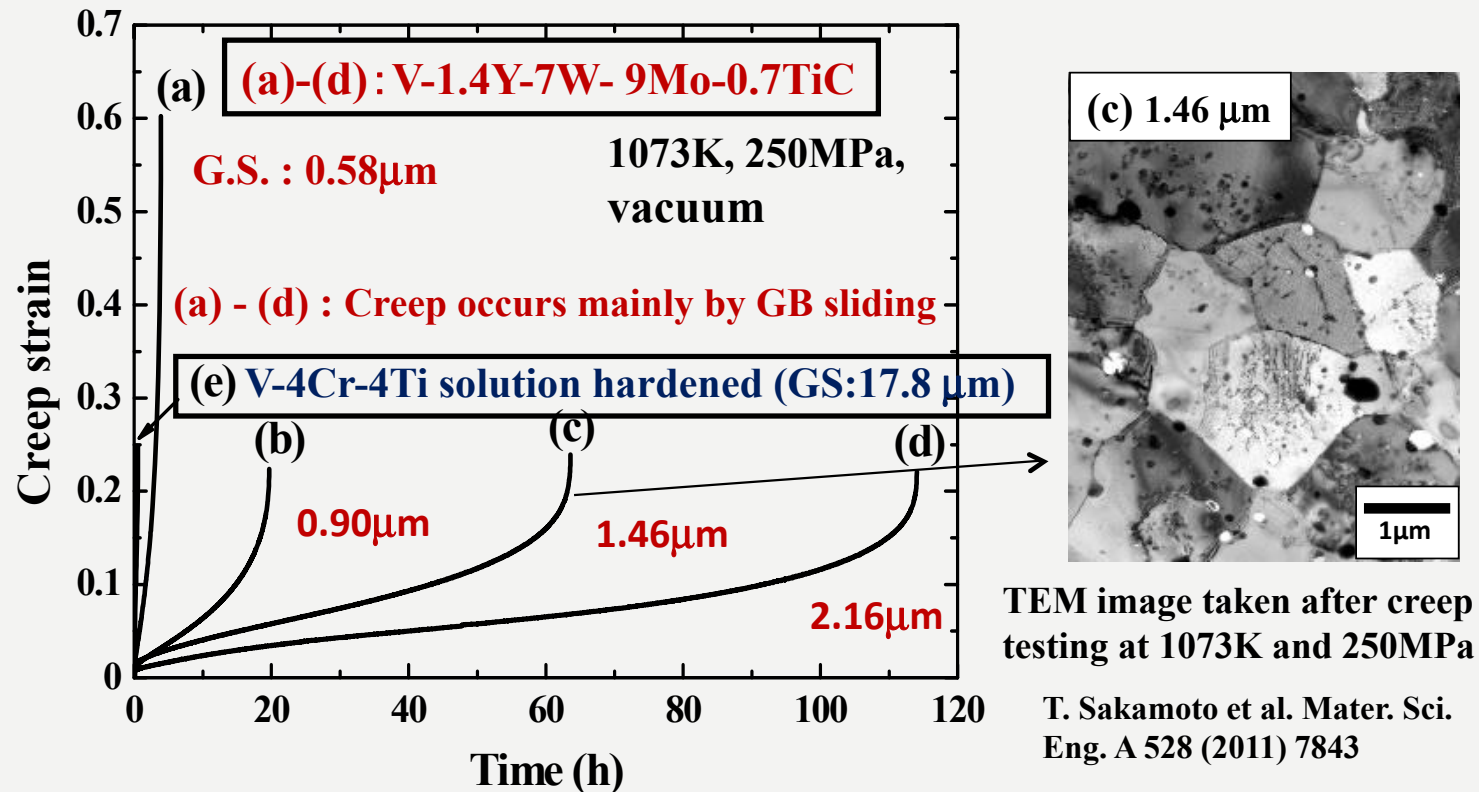
- Significantly reinforced GBs by segregation (enrichment) and precipitation of TiC_x at random GBs in the recrystallized state
- High density of sink sites for irradiation induced point defects
- Precipitation hardening
- Equiaxed fine grains (GS : 1.5 ~ 2 μm)

Need + solution hardening

+ adequate increase in grain size

Example of fine grained, solution and precipitation hardened V alloy

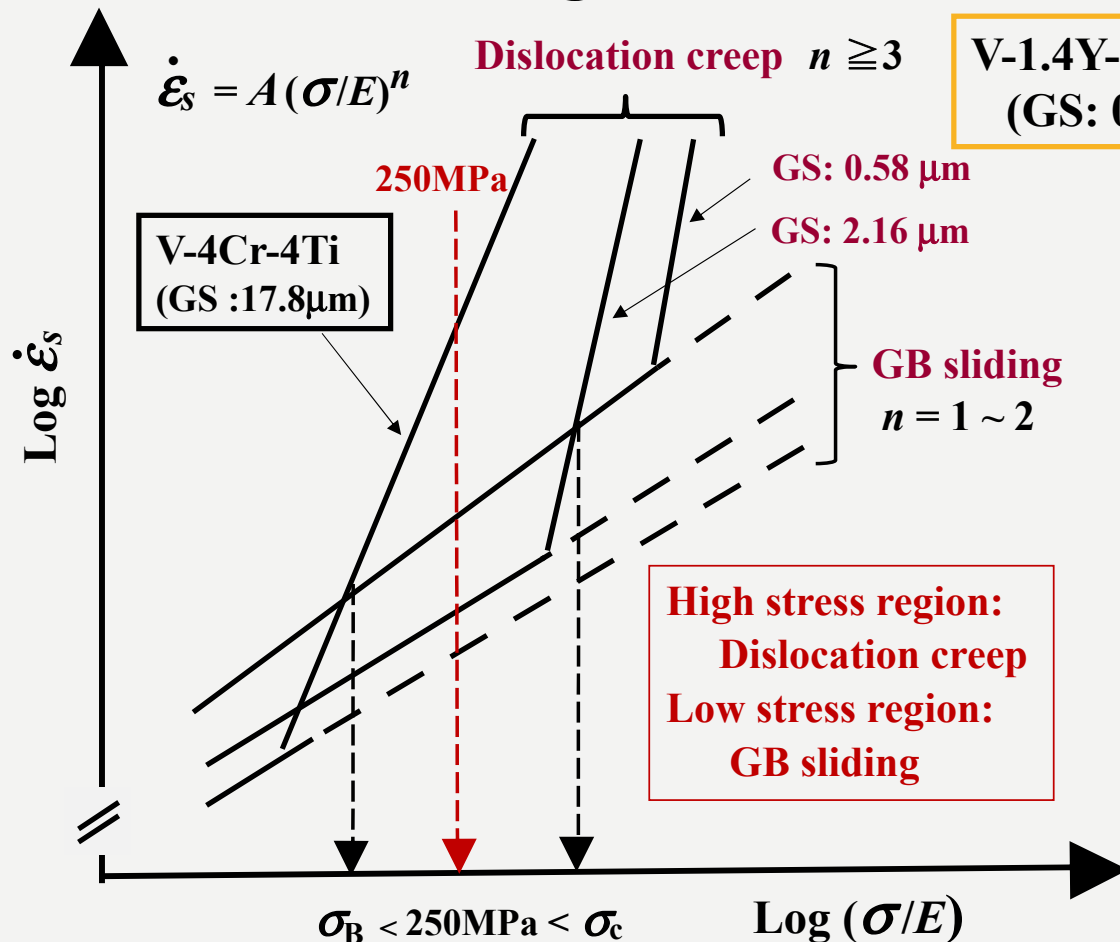
Creep resistance: Solution hardened: V-4Cr-4Ti << Solution & precipitation hardened: V-1.4Y-7W-9Mo-0.7TiC



Effects of grain size on the entire creep curve at 1073K and 250MPa for V-1.4Y-7W-9Mo-0.7TiC together with (e) V-4Cr-4Ti with grain size of 17.8 μm (Nifs heat 2).

Slight increase in grain size significantly enhances creep resistance of fine grained, solution and precipitation hardened V alloy

Relationship between steady state creep rate, $\dot{\epsilon}_s$, creep mechanism and grain size in two V alloys



V-1.4Y-7W-9Mo-0.7TiC
(GS: 0.58 ~ 2.16 μm)

T. Sakamoto et al. Mater. Sci. Eng. A 528 (2011) 7843

TFGR W-TiC is:

- Fine-grained
- Dispersion (Precipitation) hardened
- Slightly-solution hardened (Ti, C, Mo)

For increase of creep resistance,

- ◆ Addition of an appropriate element
- ◆ Control of grain-size

Subsequent effects, e.g. thermal conductivity, radiation resistance should be confirmed.

Confidential experiment will be reported in a few years.

Schematic illustration explaining the observed creep resistance for fine-grained, solution and dispersion hardened V-1.4Y-7W-9Mo-0.7TiC with different grain sizes and coarse-grained, solution hardened V-4Cr-4Ti alloy

SUMMARY

- The use of W as target material is limited by “Recrystallization embrittlement” and “Irradiation embrittlement”.
- Now the activities of TFGR W-TiC are transferred to KEK and Metal Technology Co. LTD collaboration.
- Developments are in progress under collaboration with academic and industries.
- The creep resistance of TFGR W-TiC can be improved by addition of another element and control of grain size.

Thanks for your attention and,,,

8th High Power Targetry Workshop

May 25-29, 2020

Venue : RIKEN Wako campus

Themes for the workshop include :

1. R&D to support concepts
2. Radiation damage in target material and related simulations
3. Post-irradiation examination
4. Target design, analysis and validation of concepts
5. Target facility challenges
6. Construction, fabrication, inspection, quality assurance
7. Operation of targets and beam dumps
8. Multipurpose use of targets and beam dumps

 <http://indico2.riken.jp/event/3102/>

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